1PS66SB82; 1PS88SB82

 15 V, 30 mA low C_d Schottky barrier diodes

 Rev. 04 - 13 January 2010

Product data sheet

1. **Product profile**

1.1 General description

Epitaxial low capacitance Schottky barrier diodes encapsulated in very small SMD plastic packages.

Table 1. **Product overview**

Type number	Package		Configuration
	NXP	JEITA	_
1PS66SB82	SOT666	-	triple isolated diode
1PS88SB82	SOT363	SC-88	triple isolated diode

1.2 Features

- Low diode capacitance
- Low forward voltage
- Very small SMD plastic packages

1.3 Applications

- Digital applications:
 - Ultra high-speed switching
 - Clamping circuits
- RF applications:
 - Diode ring mixer
 - RF detector
 - RF voltage doubler

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	continuous forward current		-	-	30	mA
V _R	continuous reverse voltage	1	-	-	15	V
C _d	diode capacitance	V _R = 0 V; f = 1 MHz; see <u>Figure 4</u>	-	1	-	pF



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Pinning information 2.

Table 3.	Pinning		
Pin	Description	Simplified outline Symbol	
1	anode (diode 1)		
2	anode (diode 2)		4
3	anode (diode 3)		本一
4	cathode (diode 3)		3
5	cathode (diode 2)		s sym046
6	cathode (diode 1)	001aab555	

Ordering information 3.

Table 4. Orderi	ng informati	on	
Type number	Package		
	Name	Description	Version
1PS66SB82	-	plastic surface mounted package; 6 leads	SOT666
1PS88SB82	SC-88	plastic surface mounted package; 6 leads	SOT363

Marking 4.

Table 5.	Marking codes		
Type num	nber	Marking code	
1PS66SB	82	N5	
1PS88SB	82	E1*	

[1] * = -: made in Hong Kong * = p: made in Hong Kong

- * = t: made in Malaysia
- * = W: made in China

Limiting values 5.

Table 6. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _R	continuous reverse voltage		-	15	V
I _F	continuous forward current		-	30	mA
Tj	junction temperature		-	125	°C
T _{amb}	ambient temperature		-65	+125	°C
T _{stg}	storage temperature		-65	+150	°C

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6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	SOT666		[2][3]	-	700	K/W
	SOT363		[3][4]	-	416	K/W
						-

[1] For Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and I_{F(AV)} rating will be available on request.

- [2] Refer to SOT666 standard mounting conditions.
- [3] Reflow soldering is the only recommended soldering method.
- [4] Refer to SOT363 (SC-88) standard mounting conditions.

7. Characteristics

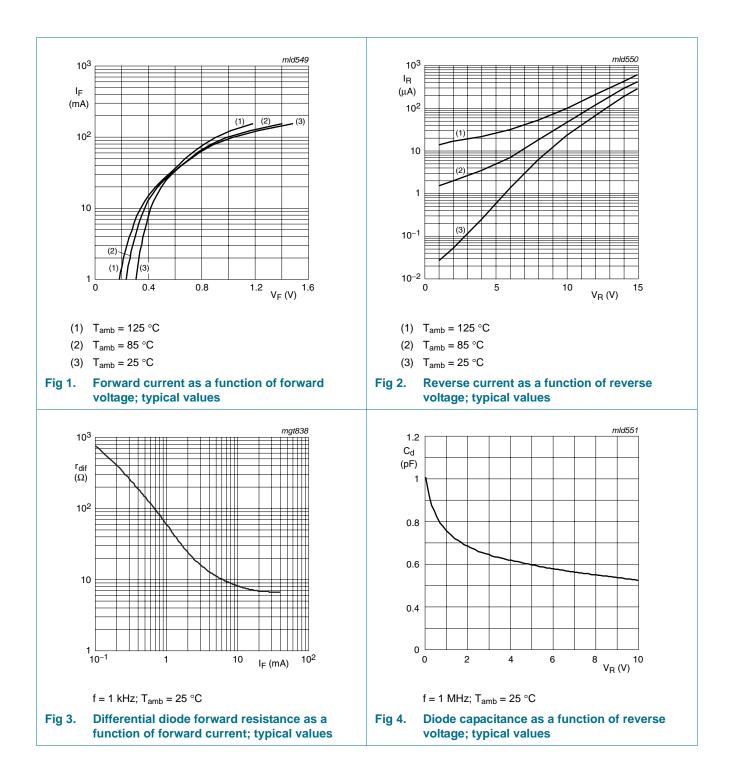
Table 8.Characteristics $T_{amb} = 25 \ ^{\circ}C$ unless otherwise specified.						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F	forward voltage	see Figure 1	<u>[1]</u>			
		I _F = 1 mA	-	-	340	mV
		I _F = 30 mA	-	-	700	mV
I _R	reverse current	V _R = 1 V; see Figure 2	-	-	0.2	μA
r _{dif}	differential resistance	I _F = 5 mA; f = 1 kHz; see <u>Figure 3</u>	-	12	-	Ω
C _d	diode capacitance	$V_R = 0 V; f = 1 MHz;$ see <u>Figure 4</u>	-	1	-	pF

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8. Package outline

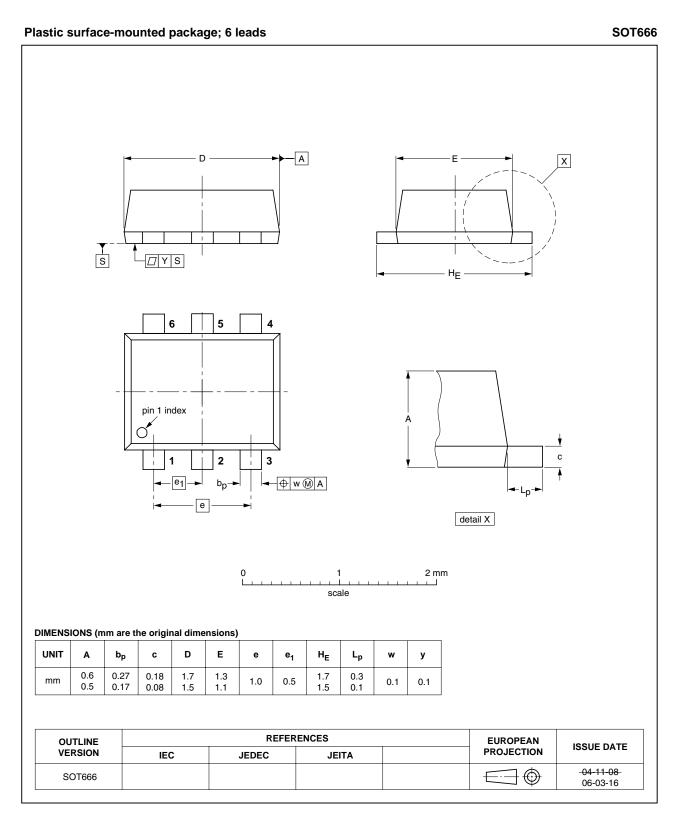


Fig 5. Package outline SOT666

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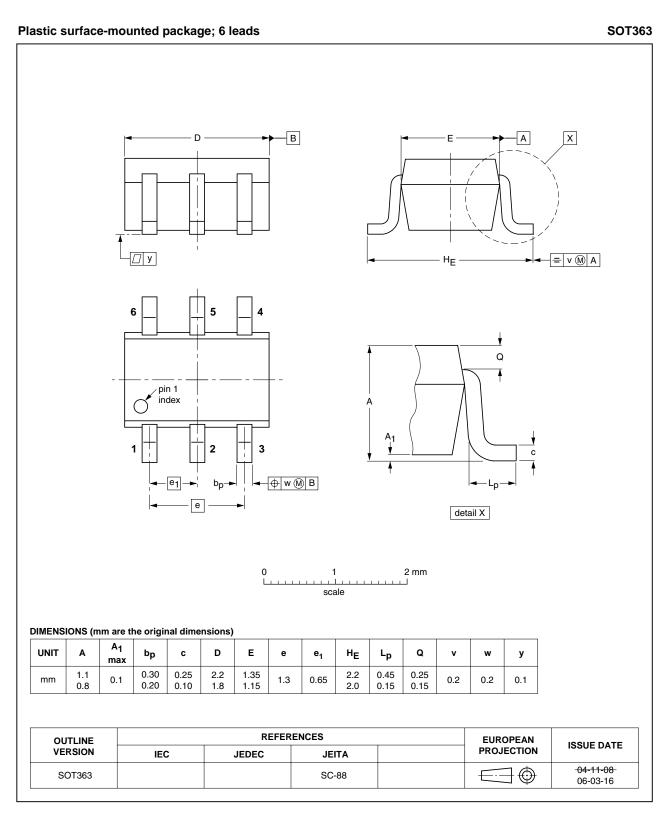


Fig 6. Package outline SOT363 (SC-88)

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9. Packing information

Table 9. Packing methods

The -xxx numbers are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing qu	antity	
			3 000	4000	10 000
1PS66SB82	SOT666	4 mm pitch, 8 mm tape and reel	-	-115	-
1PS88SB82	SOT363	4 mm pitch, 8 mm tape and reel	-115	-	-135

[1] For further information and the availability of packing methods see <u>Section 12</u>.

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10. Revision history

Table 10. Revision history	,			
Document ID	Release date	Data sheet status	Change notice	Supersedes
1PS66SB82_1PS88SB82_4	20100113	Product data sheet	-	1PS66SB82_1PS88SB82_3
Modifications:	including new content.	legal definitions and disc		name NXP Semiconductors, s were made to the technical
	 Table 3 "Pinnir 	ng": updated		
	Figure 5 "Pack	kage outline SOT666": u	pdated	
	 Figure 6 "Pack 	age outline SOT363 (So	C-88)": updated	
1PS66SB82_1PS88SB82_3	20050124	Product data sheet	-	1PS88SB82_2
1PS88SB82_2	20030411	Product specification	-	1PS88SB82_1
1PS88SB82_1	20010216	Product specification	-	-

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11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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